

**KS54AHCT 843/844**  
**KS74AHCT**

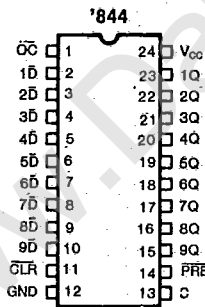
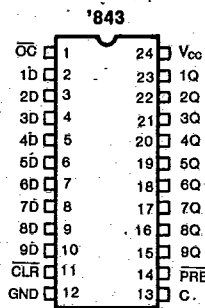
**9-Bit Bus Interface D-Type Latches with 3-State Outputs**

T-46-07-05

**FEATURES**

- Bus-Structured Pinout
- Provide Extra Bus Driving Latches Necessary for Wider Address/Data Paths or Buses with Parity
- Power-Up High Impedance
- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- 3-State outputs with high drive current (I<sub>OL</sub> = 24 mA @ V<sub>OL</sub> = 0.5V) for direct bus interface
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:  
 KS74AHCT: -40°C to +85°C  
 KS54AHCT: -55°C to +125°C
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

**PIN CONFIGURATIONS**



**DESCRIPTION**

These 9-bit bus interface latches feature three-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. They are suitable for implementing wider buffer registers, I/O ports, bidirectional bus drivers and working registers.

The nine latches are transparent D-type. The '843 has noninverting data (D) inputs and the '844 has inverting  $\bar{D}$  inputs.

A buffered output control ( $\overline{OC}$ ) input can be used to place the nine outputs in either a normal logic state (high or low levels) or a high-impedance state. The high-impedance state and increased drive provide the capability to drive the bus lines in a bus-organized system without need for interface or pull-up components.

The output control ( $\overline{OC}$ ) does not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are off.

These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to V<sub>CC</sub> and ground.

**FUNCTION TABLES**

'843

INPUTS					OUTPUT
PRE	CLR	$\overline{OC}$	C	D	Q
L	X	L	X	X	H
H	L	L	X	X	L
H	H	L	H	L	L
H	H	L	H	H	H
H	H	L	L	X	Q <sub>0</sub>
X	X	H	X	X	Z

'844

INPUTS					OUTPUT
PRE	CLR	$\overline{OC}$	C	$\bar{D}$	Q
L	X	L	X	X	H
H	L	L	X	X	L
H	H	L	H	L	H
H	H	L	H	H	L
H	H	L	L	X	Q <sub>0</sub>
X	X	H	X	X	Z

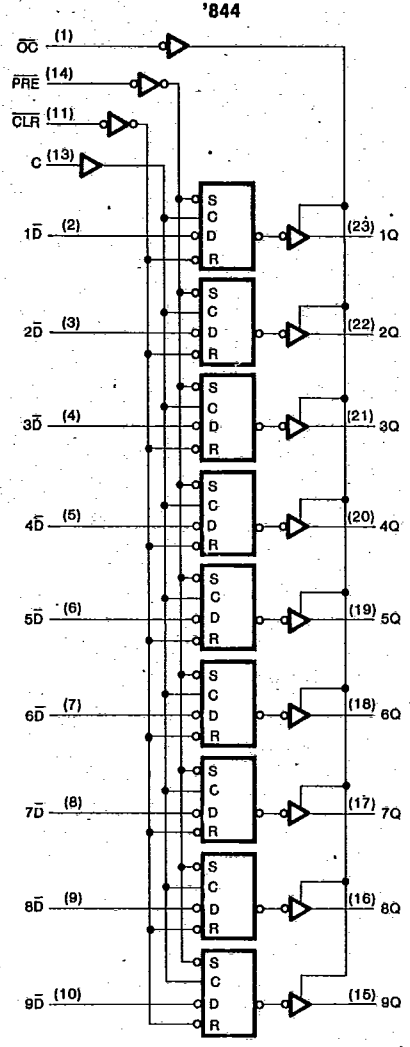
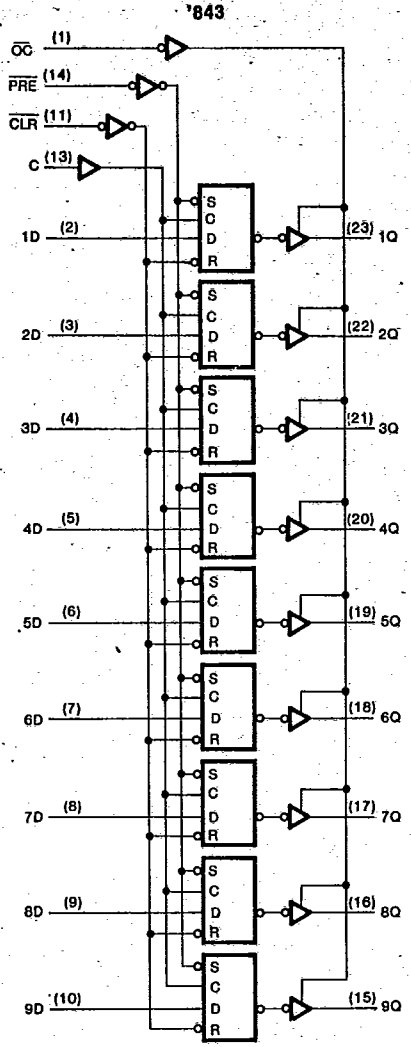
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**LOGIC DIAGRAMS**



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**Absolute Maximum Ratings\***

Supply Voltage Range  $V_{CC}$ , . . . . . -0.5V to +7V  
 DC Input Diode Current,  $I_{IK}$   
 ( $V_I < -0.5V$  or  $V_I > V_{CC} + 0.5V$ ) . . . . .  $\pm 20$  mA  
 DC Output Diode Current,  $I_{OK}$   
 ( $V_O < -0.5V$  or  $V_O > V_{CC} + 0.5V$ ) . . . . .  $\pm 20$  mA  
 Continuous Output Current Per Pin,  $I_O$   
 ( $-0.5V < V_O < V_{CC} + 0.5V$ ) . . . . .  $\pm 70$  mA  
 Continuous Current Through  
 $V_{CC}$  or GND pins . . . . .  $\pm 250$  mA  
 Storage Temperature Range,  $T_{stg}$  . . . . . -65°C to +150°C  
 Power Dissipation Per Package,  $P_d$ † . . . . . 500 mW

\* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:  
 Plastic Package (N): -12mW/°C from 65°C to 85°C  
 Ceramic Package (J): -12mW/°C from 100°C to 125°C

**Recommended Operating Conditions**

Supply Voltage,  $V_{CC}$  . . . . . 4.5V to 5.5V  
 DC Input & Output Voltages\*,  $V_{IN}$ ,  $V_{OUT}$  . . . . . 0V to  $V_{CC}$   
 Operating Temperature  
 Range KS74AHCT: -40°C to +85°C  
 KS54AHCT: -55°C to +125°C  
 Input Rise & Fall Times,  $t_r$ ,  $t_f$  . . . . . Max 500 ns  
 \* Unused inputs must always be tied to an appropriate logic voltage level (either  $V_{CC}$  or GND)

**DC ELECTRICAL CHARACTERISTICS** ( $V_{CC}=5V \pm 10\%$  Unless Otherwise Specified)

Characteristic	Symbol	Test Conditions	$T_a = 25^\circ C$			Unit	
			Typ	KS74AHCT $T_a = -40^\circ C$ to $+85^\circ C$	KS54AHCT $T_a = -55^\circ C$ to $+125^\circ C$		Guaranteed Limits
Minimum High-Level Input Voltage	$V_{IH}$			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	$V_{IL}$			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	$V_{OH}$	$V_{IN}=V_{IH}$ or $V_{IL}$ $I_O = -20\mu A$ $I_O = -6mA$	$V_{CC}$ 4.2	$V_{CC} - 0.1$ 3.98	$V_{CC} - 0.1$ 3.84	$V_{CC} - 0.1$ 3.7	V
Maximum Low-Level Output Voltage	$V_{OL}$	$V_{IN}=V_{IH}$ or $V_{IL}$ $I_O = 20\mu A$ $I_O = 12mA$ $I_O = 24mA$	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	$I_{IN}$	$V_{IN}=V_{CC}$ or GND		$\pm 0.1$	$\pm 1.0$	$\pm 1.0$	$\mu A$
Maximum 3-State Leakage Current	$I_{OZ}$	Output Enable = $V_{IH}$ $V_{OUT}=V_{CC}$ or GND		$\pm 0.5$	$\pm 5.0$	$\pm 10.0$	$\mu A$
Maximum Quiescent Supply Current	$I_{CC}$	$V_{IN}=V_{CC}$ or GND $I_{OUT}=0\mu A$		8.0	80.0	160.0	$\mu A$
Additional Worst Case Supply Current	$\Delta I_{CC}$	per input pin $V_I = 2.4V$ other inputs: at $V_{CC}$ or GND $I_{OUT}=0\mu A$		2.7	2.9	3.0	mA

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**AC ELECTRICAL CHARACTERISTICS** (Input  $t_r, t_f \leq 2$  ns), AHCT843, AHCT844

Characteristic	Symbol	Conditions†	T <sub>a</sub> = 25°C V <sub>CC</sub> = 5.0V		KS74AHCT T <sub>a</sub> = -40°C to +85°C V <sub>CC</sub> = 5.0V ± 10%		KS54AHCT T <sub>a</sub> = -55°C to +125°C V <sub>CC</sub> = 5.0V ± 10%		Unit
			Typ	Min	Max	Min	Max		
			Propagation Delay, Data to Q	t <sub>PLH</sub>	C <sub>L</sub> = 50pF C <sub>L</sub> = 150pF	13 16		18 23	
	t <sub>PHL</sub>	C <sub>L</sub> = 50pF C <sub>L</sub> = 150pF	13 16		18 23		22 28		
Propagation Delay, C to any Q	t <sub>PLH</sub>	C <sub>L</sub> = 50pF C <sub>L</sub> = 150pF	16 19		26 31		31 37	ns	
	t <sub>PHL</sub>	C <sub>L</sub> = 50pF C <sub>L</sub> = 150pF	16 19		26 31		31 37		
Propagation Delay, PRE to Q	t <sub>PLH</sub>	C <sub>L</sub> = 50pF C <sub>L</sub> = 150pF	17 20		27 32		32 38	ns	
Propagation Delay, CLR to Q	t <sub>PHL</sub>	C <sub>L</sub> = 50pF C <sub>L</sub> = 150pF	17 20		27 32		32 38	ns	
Output Enable Time, OC to any Q	t <sub>PZL</sub>	R <sub>L</sub> = 1kΩ C <sub>L</sub> = 50pF C <sub>L</sub> = 150pF	11 14		18 23		22 28	ns	
	t <sub>PZL</sub>		11 14		18 23		22 28		
Output Disable Time, OC to any Q	t <sub>PHZ</sub>	R <sub>L</sub> = 1kΩ	13		18		22	ns	
	t <sub>PLZ</sub>	C <sub>L</sub> = 50pF	13		18		22		
Pulse Width, C High	t <sub>w</sub>		12	20		25		ns	
Setup Time, Data before C↓	t <sub>SU</sub>		8	10		12		ns	
Hold Time, Data after C↓	t <sub>H</sub>		3	5		7		ns	
Input Capacitance	C <sub>IN</sub>		5					pF	
Output Capacitance	C <sub>OUT</sub>	Output Disabled	10					pF	
Power Dissipation Capacitance* (per stage)	C <sub>PD</sub>	OC = V <sub>CC</sub>	5					pF	
		OC = GND	30						

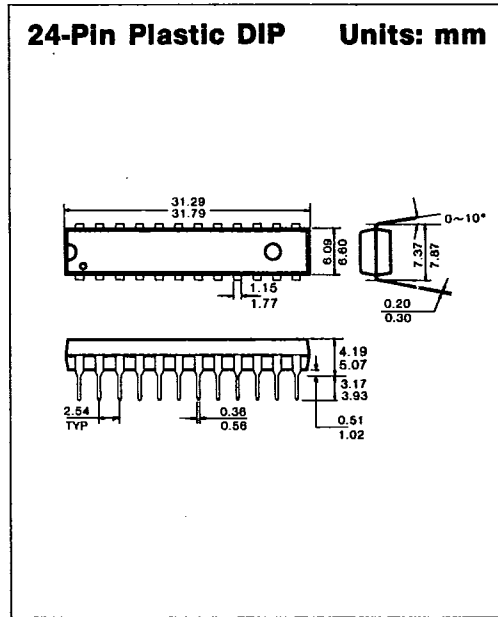
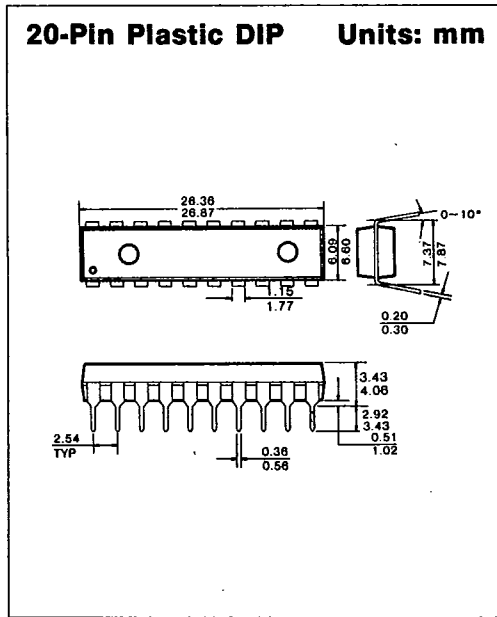
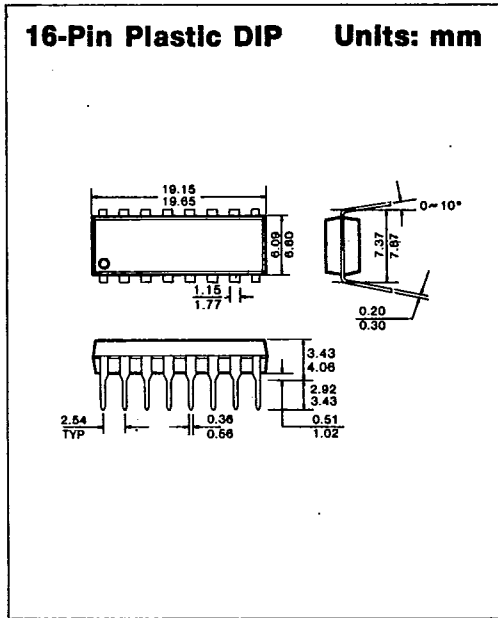
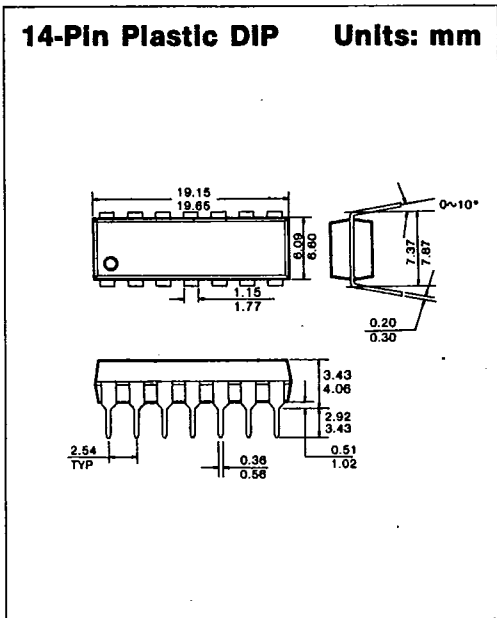
\* C<sub>PD</sub> determines the no-load dynamic power dissipation: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup> f + I<sub>CC</sub> V<sub>CC</sub>.

† For AC switching test circuits and timing waveforms see section 2.

**PACKAGE DIMENSIONS**

T-90-20

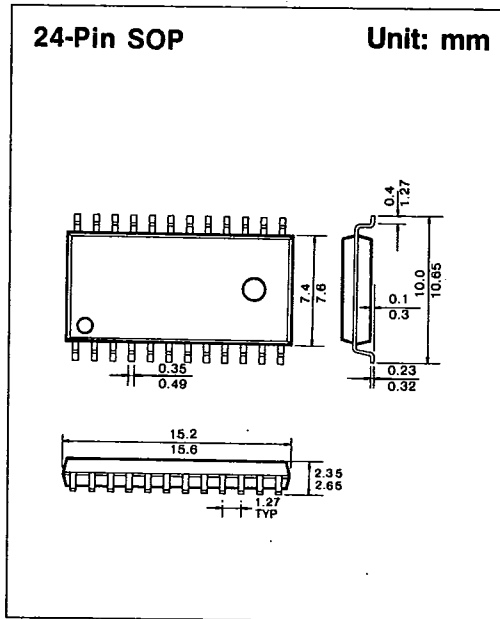
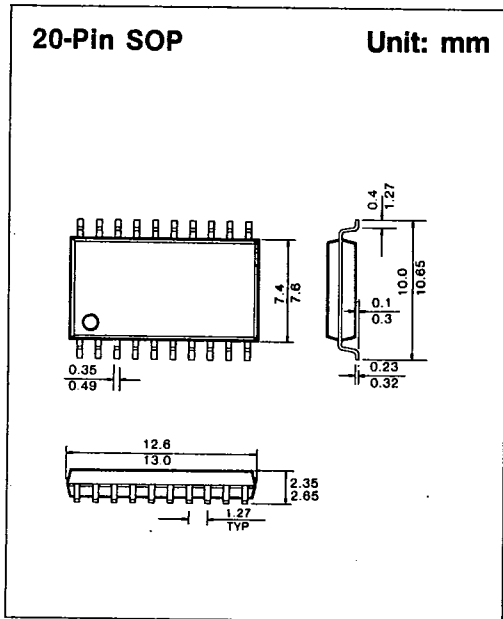
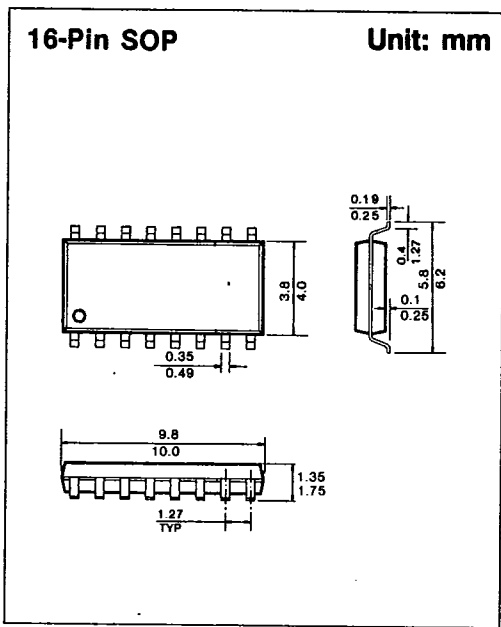
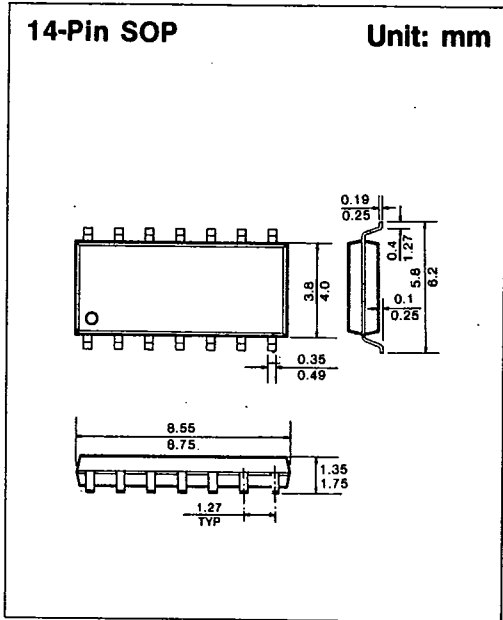
**1. PLASTIC PACKAGES**



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**PACKAGE DIMENSIONS**

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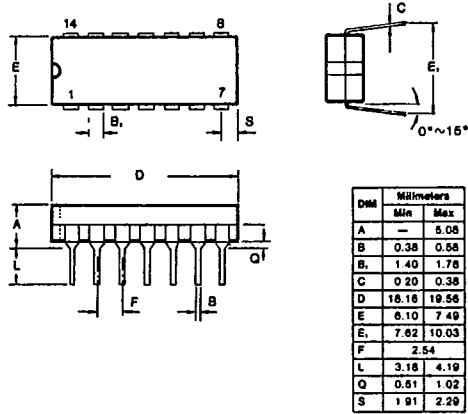


**PACKAGE DIMENSIONS**

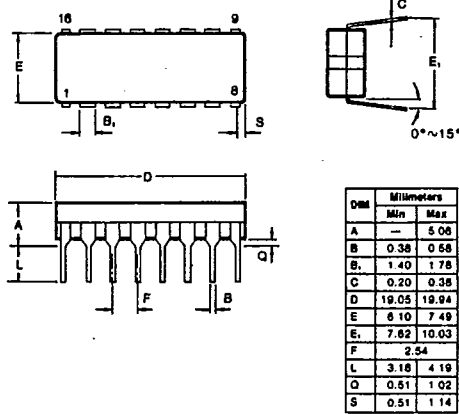
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**2. CERAMIC PACKAGES**

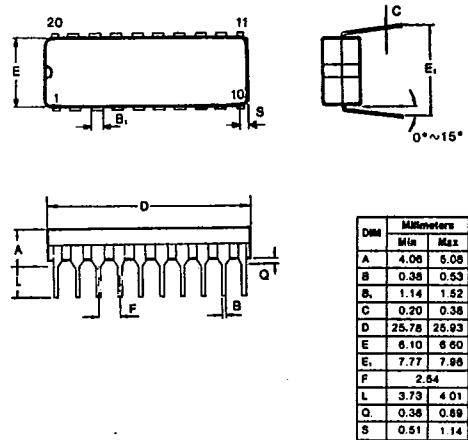
**14-Pin Ceramic DIP Units: mm**



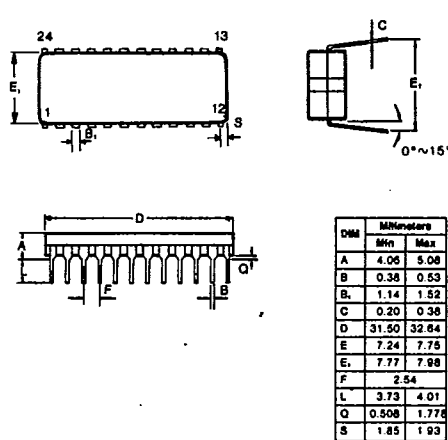
**16-Pin Ceramic DIP Units: mm**



**20-Pin Ceramic DIP Units: mm**



**24-Pin Ceramic DIP Units: mm**



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